

Driver Transistors

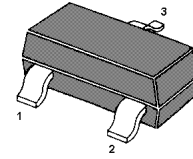
NPN Silicon

MAXIMUM RATINGS

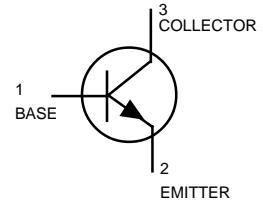
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	80	Vdc
Collector–Base Voltage	V_{CBO}	120	Vdc
Emitter–Base Voltage	V_{EBO}	5.0	Vdc
Collector Current — Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR– 5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



CASE 318–08, STYLE 6
SOT–23 (TO–236AB)



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 4.0 \text{ mAdc}$)	$V_{(BR)CEO}$	80	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}$)	$V_{(BR)CBO}$	120	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 100 \mu\text{Adc}$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 90 \text{ Vdc}$) ($T_A = 150^\circ\text{C}$)	I_{CBO}	—	0.1 500	nAdc
Emitter Cutoff Current ($V_{EB} = 4.0 \text{ Vdc}$)	I_{EBO}	—	200	nAdc

1. FR–5 = $1.0 \times 0.75 \times 0.062 \text{ in.}$ 2. Alumina = $0.4 \times 0.3 \times 0.024 \text{ in.}$ 99.5% alumina.

Thermal Clad is a trademark of the Bergquist Company.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
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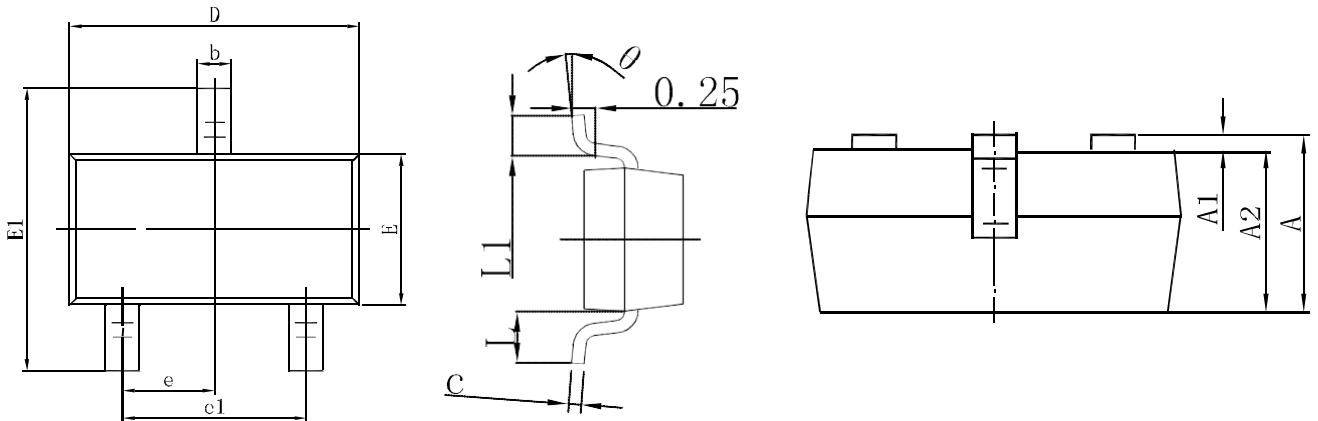
ON CHARACTERISTICS

DC Current Gain ($I_C = 10 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	h_{FE}	20	—	—
Collector–Emitter Saturation Voltage ($I_C = 4.0 \text{ mAdc}$, $I_B = 0.4 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}$, $I_B = 15 \text{ mAdc}$)	$V_{CE(sat)}$	—	0.15 0.2	Vdc
Forward Base–Emitter Voltage	$V_{BE(sat)}$	—	—	—

SMALL–SIGNAL CHARACTERISTICS

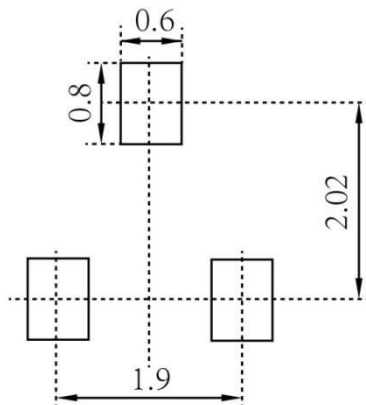
Current–Gain — Bandwidth Product ($I_C = 4.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 20 \text{ MHz}$)	f_T	60	—	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	C_{ob}	—	20	pF

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only